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APPLICANT

Toshiya Yokogawa, et al.

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U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.	pc	4,882,609	11/21/1989	Schubert, et al.	_____	

FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.	pc	EP 0612104A2	08/24/1994	Europe			
2.	pc	WO 01/93339 A1	12/6/2001	WIPO		Abstract	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

Ref. Desig.	Examiner's Initials	
1.	pc	"Characterization of Double Pulse-Doped Channel GaAs MESFET's", Shigeru Nakajima, et al., IEEE Electron Device Letters, Vol. 14, No. 3, March 1993, pp. 146-148.
2.	pc	"Stark Effect Studied in δ -doped GaAs Structures", A. Ben Jazia, et al., Semicond. Sci. Technol. 12 (1997), pp. 1988-1395.
3.	pc	"Vertical Hot-Wall Type CVD for SiC Growth", Kunimasa Takahashi, et al., Materials Science Forum Vols. 338-342 (2000), pp. 141-144.
4.	pc	"Electronic Properties of Nitrogen Delta-Doped Silicon Carbide Layers", Toshiya Yokogawa, et al., Mat. Res. Soc. Symp. Proc. Vol. 640 (2001), pp. H2.5.1-H2.5.6.
5.	pc	Partial Supplementary European Search Report EP 00 97 6350, 12/20/2002.

Examiner: PHAT X. CAO

Date Considered: 3/20/03

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